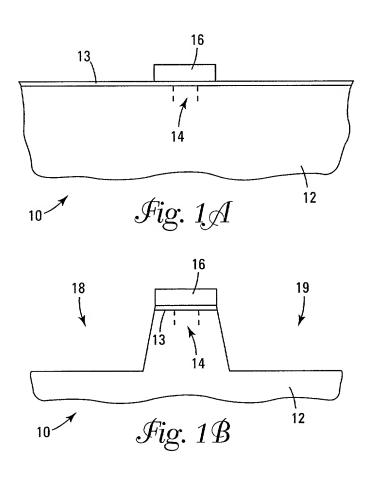
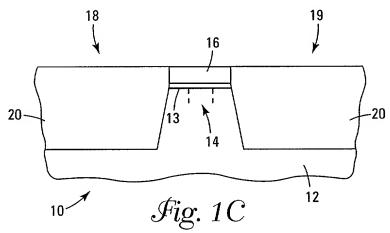
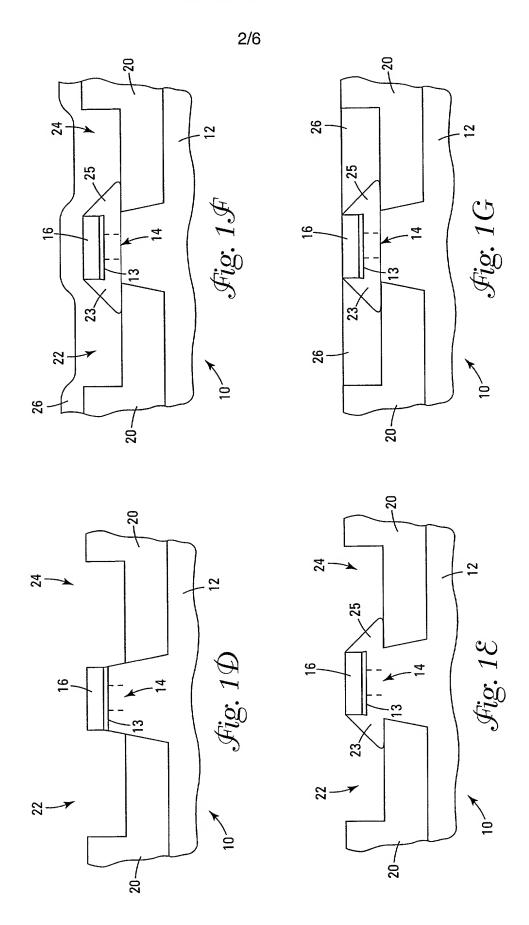
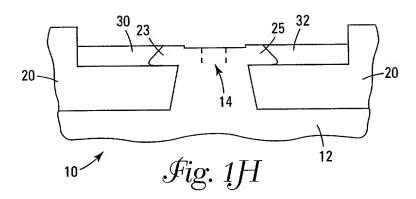
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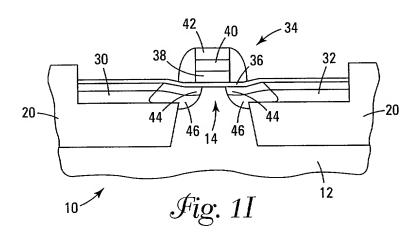


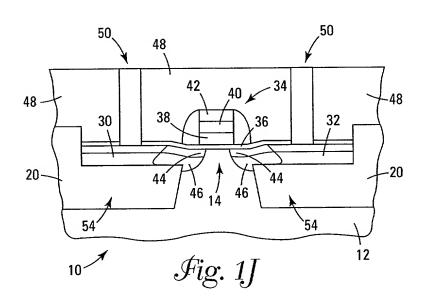


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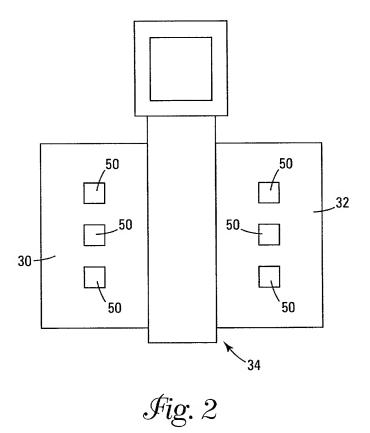






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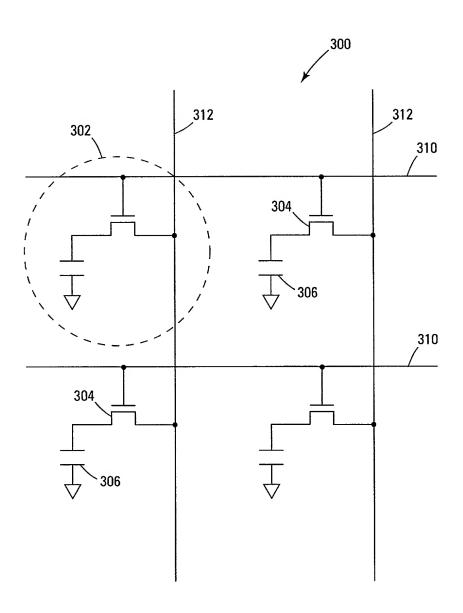


Fig. 3

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